

8-Pin Dual Channel Phototransistor Optocoupler

MCT9001

Description

The general purpose optocoupler, MCT9001, has two isolated channels in a standard plastic 8-pin dual-in-line (DIP) package for density applications. Each channel consists of a gallium arsenide infrared emitting diode driving a NPN silicon planar phototransistor. For four channel applications, two packages fit into a standard 16-pin DIP socket.

Features

- Two Isolated Channels Per Package
- Safety and Regulatory Approvals:
 - UL1577, 4,170 VAC_{RMS} for 1 Minute
 - ◆ DIN-EN/IEC60747-5-5, 890 V Peak Working Insulation Voltage
- These are Pb-Free Devices

Applications

- AC Line/Digital Logic Isolate High Voltage Transients
- Digital Logic/Digital Logic Eliminate Spurious Ground
- Digital Logic/AC Triac Control Isolate High Voltage Transients
- Twisted Pair Line Receiver Eliminate Ground Loop Feedthrough
- Telephone/Telegraph Line Receiver Isolate High Voltage Transients
- High Frequency Power Supply Feedback Control Maintain Floating Grounds and Transients
- Relay Contact Monitor Isolate Floating Grounds and Transients
- Power Supply Monitor Isolate Transients



PDIP8 9.655x6.6, 2.54P CASE 646CQ



PDIP8 GW CASE 709AF



PDIP8 9.68x6.5, 2.54P CASE 646CJ

MARKING DIAGRAM

MCT9001 VXYYH

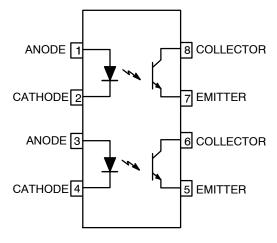
MCT9001 = Device Code

V = DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option) X = One Digit Year Code

X = One Digit Year Code YY = Digit Work Week

H = Assembly Package Code

FUNCTIONAL SCHEMATIC



Equivalent Circuit

ORDERING INFORMATION

See detailed ordering and shipping information in the ordering information section on page 6 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 6.

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SAFETY AND INSULATION RATINGS (As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.)

Parameter		Characteristics
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage	<150 V _{RMS}	I–IV
For Hated Mains Voltage <300 V _{RMS}		I–IV
Climatic Classification		55/115/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V _{PR}	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10 \text{ s}$, Partial Discharge <5 pC	1424	V _{peak}
	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge <5 pC	1668	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	890	V_{peak}
V _{IOTM}	Highest Allowable Over-Voltage	8000	V _{peak}
	External Creepage	≥ 7.0	mm
	External Clearance	≥ 7.0	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T _S	Case Temperature (Note 1)	175	°C
I _{S,INPUT}	Input Current (Note 1)	60	mA
P _{S,OUTPUT}	Output Power (Note 1)	150	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	>10 ⁹	Ω

^{1.} Safety limit value - maximum values allowed in the event of a failure.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified.)

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	-55 to +150	°C
T _{OPR}	Operating Temperature	-55 to +100	°C
TJ	Junction Temperature	-55 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 s	°C
P _D	Total Device Power Dissipation @T _A = 25°C	400	mW
	Derate Above 25°C	4.83	mW/°C
EMITTER (EACH	CHANNEL)		
I _F	DC / Average Forward Input Current	60	mA
I _F (pk)	Forward Current – Peak (PW = 1 μs, 300 pps)	3	Α
V_{R}	Reverse Input Voltage	5.0	W
P _{D(EMITTER)}	Total Power Dissipation @T _A = 25°C	100	mW
	Derate Above 25°C	1.1	mW/°C
DETECTOR			
I _C	Continuous Collector Current	30	mA
P _{D(DETECTOR)}	Total Power Dissipation @T _A = 25°C	150	mW
	Derate Above 25°C	1.67	mW/°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
EMITTER		•				
V _F	Input Forward Voltage	I _F = 10 mA	-	1.0	1.3	V
I _R	Reverse Leakage Current	V _R = 5 V	-	-	10	μΑ
CJ	Junction Capacitance	V _F = 0 V, f = 1 MHz	-	50	-	pF
DETECTO	R					
BV _{CEO}	Collector-to-Emitter Breakdown Voltage	I _C = 0.5 mA, I _F = 0	55	_	-	V
BV _{ECO}	Emitter-to-Collector Breakdown Voltage	I _E = 100 μA, I _F = 0	7	-	-	V
I _{CEO}	Collector-Emitter Dark Current	V _{CE} = 24 V, I _F = 0	-	5	100	nA
		V _{CE} = 24 V, T _A = 85°C	-	_	50	μΑ
C _{CE}	Capacitance	V _{CE} = 0 V, f = 1.0 MHz	-	8	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TRANSFER CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
DC CHARACTERISTICS						
CTR	Current Transfer Ratio, Collector-to-Emitter	I _F = 5 mA, V _{CE} = 5 V	50	-	600	%
CTR(SAT)	Collector-to-Emitter	I _F = 8 mA, V _{CE} = 0.4 V	30	_	-	%
VCE(SAT)	Saturation Voltage, Collector-to-Emitter	I _F = 8 mA, I _C = 2.4 mA	-	_	0.4	V

AC CHARACTERISTICS

Non-Saturated

T _{ON}	Turn-On Time	R_L = 100 Ω , I_C = 2 mA, V_{CC} = 10 V	ı	3.0	-	μs
T _{OFF}	Turn-Off Time		-	3.0	-	μs
T _R	Rise Time		-	2.4	-	μs
T _F	Fall Time		ı	2.4	-	μs
Saturated						

Saturated

Ton	Turn-On Time	$I_F = 16 \text{ mA}, R_L = 1.9 \text{ k}\Omega, V_{CE} = 5 \text{ V}$	ı	2.4	1	μs
Toff	Turn-Off Time		-	25.0	_	μs

ISOLATION CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
V _{ISO}	Input-Output Isolation Voltage	$I_{I-O} \le 10 \ \mu A$, t = 1 min	5,000	-	-	VAC _{RMS}
C _{ISO}	Isolation Capacitance	f = 1 MHz	-	0.5	-	pF
R _{ISO}	Isolation Resistance	V _{I-O} = 500 V _{DC}	10 ¹¹	_	ı	Ω

TYPICAL PERFORMANCE CURVES

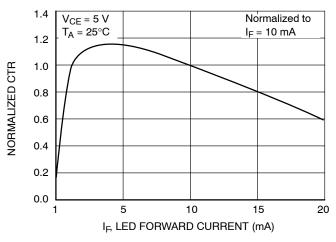


Figure 1. Normalized CTR vs. Forward Current

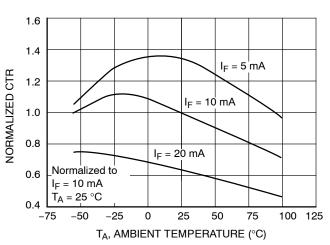


Figure 2. Normalized CTR vs. Ambient Temperature

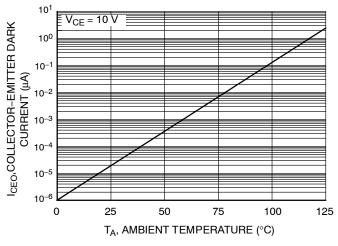


Figure 3. Dark Current vs. Ambient Temperature

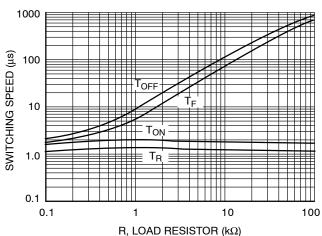


Figure 4. Switching Speed vs. Load Resistor

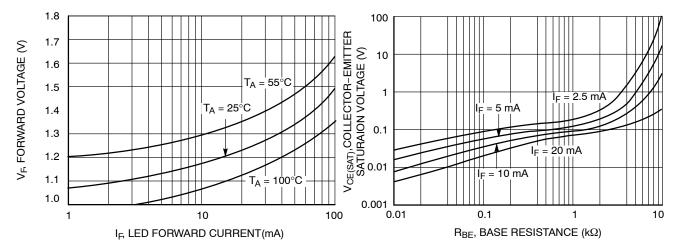


Figure 5. LED Forward Voltage vs. Forward Current

Figure 6. Collector-Emitter Saturation Voltage vs. Collector Current

SWITCHING TIME TEST CIRCUIT AND WAVEFORMS

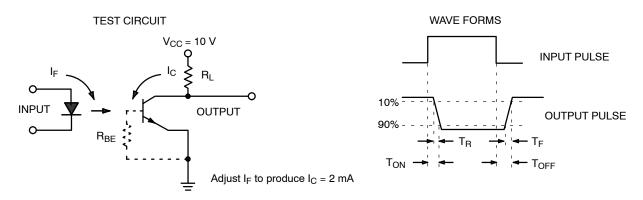


Figure 7. Switching Time Test Circuit and Waveforms

REFLOW PROFILE

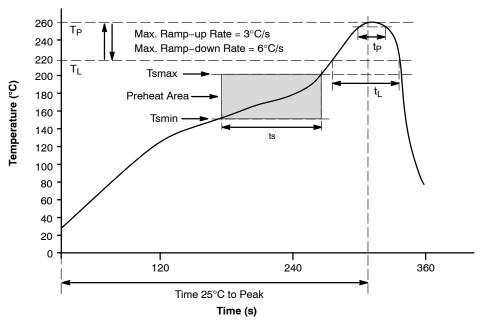


Figure 8. Reflow Profile

REFLOW PROFILE

Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60 – 120 s
Ramp-up Rate (t _L to t _P)	3°C/s max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 s
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 s
Ramp-down Rate (T _P to T _L)	6°C / s max.
Time 25°C to Peak Temperature	8 min max.

ORDERING INFORMATION

Device	Description	Shippping [†]
MCT9001	DIP 8-Pin	1000 Units / Tube
MCT9001S	SMT 8-Pin (Lead Bend)	1000 Units / Bulk
MCT9001SD	SMT 8-Pin	1000 Units / Tape & Reel

DISCONTINUED (Note 2)

MCT9001300	DIN EN/IEC 60747-5-5 Option	50 Units / Tube
MCT90013S	SMT 8-Pin (Lead Bend); DIN EN/IEC 60747-5-5 Option	50 Units / Tube
MCT90013SD	SMT 8-Pin; DIN EN/IEC 60747-5-5 Option	1000 Units / Tape & Reel
MCT9001300W	0.4" Lead Spacing; DIN EN/IEC 60747-5-5 Option	50 Units / Tube

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

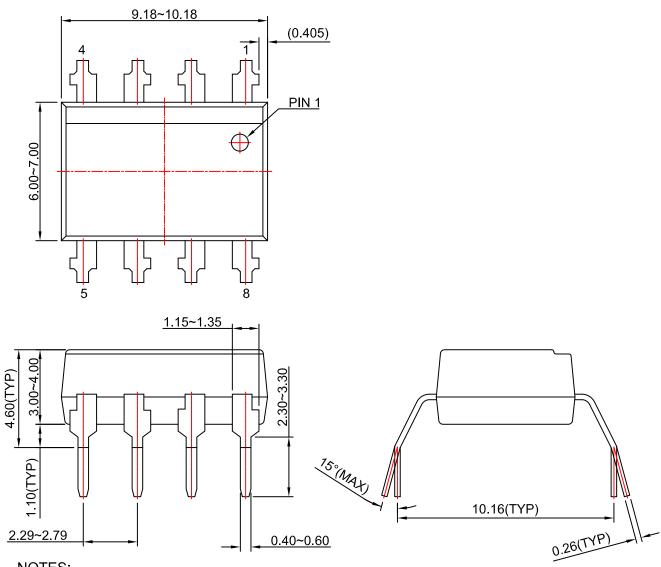
2. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most

current information on this device may be available on www.onsemi.com.

PACKAGE DIMENSIONS

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DATE 31 JUL 2016

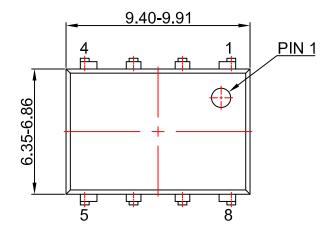


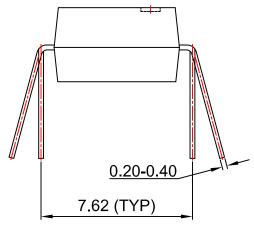
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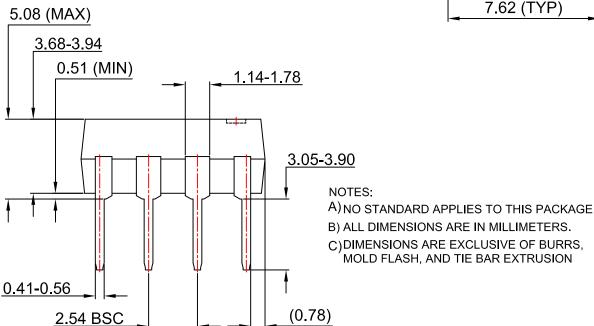


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